BAV70L, SBAV70L

Dual Switching Diode Common Cathode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	100	V
Forward Current	I _F	200	mA
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I _{FRM}	1.5	А
Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^{\circ}\text{C}$ prior to surge) $t = 1 \mu\text{S}$ $t = 10 \mu\text{S}$ $t = 100 \mu\text{S}$ $t = 100 \mu\text{S}$ $t = 1 \text{ms}$ $t = 10 \text{ms}$ $t = 10 \text{ms}$ $t = 10 \text{ms}$ $t = 15 \text{ms}$ $t = 15 \text{ms}$ $t = 15 \text{ms}$	I _{FSM}	31 16 10 4.5 2.5 1.0 0.5	A

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_{\Delta} = 25^{\circ}C$	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate,	P _D	300	mW
(Note 2) T _A = 25°C Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

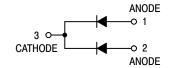


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SOT-23 (TO-236) CASE 318 STYLE 9



MARKING DIAGRAM



A4 = Device Code M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAV70LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAV70LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BAV70LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SBAV70LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

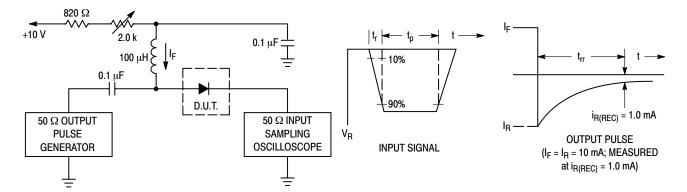
BAV70L, SBAV70L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage (I _(BR) = 100 μA)	V _(BR)	100	_	V
Reverse Voltage Leakage Current (Note 3) $ (V_R = 25 \text{ V}, T_J = 150^{\circ}\text{C}) $ $ (V_R = 100 \text{ V}) $ $ (V_R = 70 \text{ V}, T_J = 150^{\circ}\text{C}) $	I _R	- - -	60 1.0 100	μΑ
Diode Capacitance (V _R = 0 V, f = 1.0 MHz)	C _D	_	1.5	pF
Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 50 \text{ mA})$ $(I_F = 150 \text{ mA})$	V _F	- - - -	715 855 1000 1250	mV
Reverse Recovery Time $R_L = 100 \Omega$ (I _F = I _R = 10 mA, I _{R(REC)} = 1.0 mA) (Figure 1)	t _{rr}	_	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{3.} For each individual diode while second diode is unbiased.



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (IF) of 10 mA.

- 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
- 3. $t_p \gg t_r$

Figure 1. Recovery Time Equivalent Test Circuit

BAV70L, SBAV70L

Curves Applicable to Each Anode

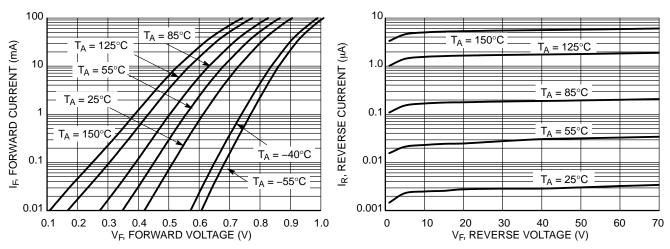


Figure 2. Forward Voltage

Figure 3. Leakage Current

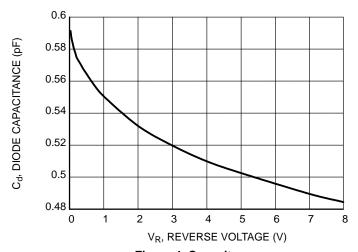


Figure 4. Capacitance



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

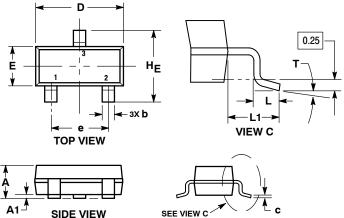
SCALE 4:1

CTVLE 4 TUDULE.

DRAIN

3. CATHODE

STYLE 27: PIN 1. CATHODE 2. CATHODE



END VIEW

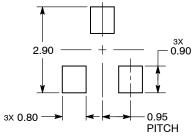
CTVLE 7

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

RECOMMENDED SOLDERING FOOTPRINT



CTVLE 6.

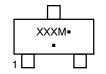
DIMENSIONS: MILLIMETERS

3. INPUT

3. ANODE

STYLE 28: PIN 1. ANODE 2. ANODE

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5:	STYLE 6:	STYLE 7:	STYLE 8:		
CANCELLED	PIN 1. BASE	PIN 1. EMITTER	PIN 1. ANODE		
	EMITTER	2. BASE	NO CONNECTION		
	COLLECTOR	3. COLLECTOR	3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	2. SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION		PIN 1. CATHODE
CATHODE	CATHODE	ANODE	CATHODE	ANODE	ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANOD	E 3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
			0.0011000	O OATE	A NO CONNECTION

CATHODE

CTVI F O

3. SOURCE

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